

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises means for simultaneously performing a first operation for changing a threshold voltage of a memory element and a second operation for judging the threshold voltage of the memory element.

115. (New) The mobile telephone according to claim 114, further comprising:

means for terminating the first operation and the second operation and finishing a verify operation at a timing when the threshold voltage of the memory element judged by the second operation becomes a set voltage.

116. (New) The mobile telephone according to claim 114, wherein the memory element stores multi-state data.

117. (New) The mobile telephone according to claim 114, wherein the memory element is an n-channel type memory element.

118. (New) The mobile telephone according to claim 114, wherein the memory element is a p-channel type memory element.

119. (New) The mobile telephone according to claim 114, wherein the nonvolatile memory is a

NOR type nonvolatile memory.

120. (New) The mobile telephone according to claim 114, wherein the nonvolatile memory is a NAND type nonvolatile memory.

121. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises means for simultaneously performing a first operation for changing a threshold voltage of a memory element by one of charge injection and charge discharge using a tunnel current and a second operation for judging the threshold voltage of the memory element.

122. (New) The mobile telephone according to claim 121, wherein a potential difference exists between a source and a drain of the memory element during the second operation.

123. (New) The mobile telephone according to claim 121, further comprising:

means for terminating the first operation and the second operation and finishing a verify operation at a timing when the threshold voltage of the memory element judged by the second operation becomes a set voltage.

124. (New) The mobile telephone according to claim 121, wherein the memory element stores multi-state data.

125. (New) The mobile telephone according to claim 121, wherein the memory element is an n-channel type memory element.

126. (New) The mobile telephone according to claim 121, wherein the memory element is a p-channel type memory element.

127. (New) The mobile telephone according to claim 121, wherein the nonvolatile memory is a NOR type nonvolatile memory.

128. (New) The mobile telephone according to claim 121, wherein the nonvolatile memory is a NAND type nonvolatile memory.

129. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises means for simultaneously performing a first operation

for changing a threshold voltage of a memory element by charge injection using a hot electron and a second operation for judging the threshold voltage of the memory element.

130. (New) The mobile telephone according to claim 129, further comprising:

means for terminating the first operation and the second operation and finishing a verify operation at a timing when the threshold voltage of the memory element judged by the second operation becomes a set voltage.

131. (New) The mobile telephone according to claim 129, wherein the memory element stores multi-state data.

132. (New) The mobile telephone according to claim 129, wherein the memory element is an n-channel type memory element.

133. (New) The mobile telephone according to claim 129, wherein the memory element is a p-channel type memory element.

134. (New) The mobile telephone according to claim 129, wherein the nonvolatile memory is a NOR type nonvolatile memory.

135. (New) The mobile telephone according to claim 129, wherein the nonvolatile memory is a NAND type nonvolatile memory.

136. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises:

means for simultaneously performing a first operation for increasing the threshold voltage of the memory element and a second operation for judging a relation between the threshold voltage of the memory element and the set voltage;

means for, during the second operation, generating a verify signal that takes a first value if the threshold voltage of the memory element is smaller than the set voltage and takes a second value if the threshold voltage of the memory element is larger than the set voltage;

means for performing the first operation if the verify signal takes the first value, and not performing the first operation if the verify signal takes the second value; and

means for terminating the first operation and the second operation and finishing the verify operation when the verify signal changes from the first value to the second value.

137. (New) The mobile telephone according to claim 136, wherein the memory element stores multi-state data .

138. (New) The mobile telephone according to claim 136, wherein the first operation is performed

by one of charge injection and charge discharge using a tunnel current.

139. (New) The mobile telephone according to claim 136, wherein during the second operation, a potential difference exists between a source and a drain of the memory element.

140. (New) The mobile telephone according to claim 136, wherein the first operation is performed by charge injection using a hot electron.

141. (New) The mobile telephone according to claim 136, wherein the memory element is an n-channel type memory element.

142. (New) The mobile telephone according to claim 136, wherein the memory element is a p-channel type memory element.

143. (New) The mobile telephone according to claim 136, wherein the nonvolatile memory is a NOR type nonvolatile memory.

144. (New) The mobile telephone according to claim 136, wherein the nonvolatile memory is a NAND type nonvolatile memory.

145. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises:

means for simultaneously performing a first operation for decreasing the threshold voltage of the memory element and a second operation for judging a relation between the threshold voltage of the memory element and the set voltage;

means for, during the second operation, generating a verify signal that takes a first value if the threshold voltage of the memory element is larger than the set voltage and takes a second value if the threshold voltage of the memory element is smaller than the set voltage;

means for performing the first operation if the verify signal takes the first value, and not performing the first operation if the verify signal takes the second value; and

means for terminating the first operation and the second operation and finishing the verify operation when the verify signal changes from the first value to the second value.

146. (New) The mobile telephone according to claim 145, wherein the memory element stores multi-state data.

147. (New) The mobile telephone according to claim 145, wherein the first operation is performed by one of charge injection and charge discharge using a tunnel current.

148. (New) The mobile telephone according to claim 145, wherein during the second operation, a

potential difference exists between a source and a drain of the memory element.

149. (New) The mobile telephone according to claim 145, wherein the first operation is performed by charge injection using a hot electron.

150. (New) The mobile telephone according to claim 145, wherein the memory element is an n-channel type memory element.

151. (New) The mobile telephone according to claim 145, wherein the memory element is a p-channel type memory element.

152. (New) The mobile telephone according to claim 145, wherein the nonvolatile memory is a NOR type nonvolatile memory.

153. (New) The mobile telephone according to claim 145, wherein the nonvolatile memory is a NAND type nonvolatile memory.

154. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises:

means for simultaneously performing a first operation for increasing the threshold voltage of the memory element and a second operation for judging a relation between the threshold voltage of the memory element and the set voltage;

means for generating a verify signal that takes a first value during a first period;

means for, during a second period, generating a verify signal that takes the first value if the threshold voltage of the memory element is smaller than the set voltage, and takes a second value if the threshold voltage of the memory element is larger than the set voltage;

means for performing the first operation if the verify signal takes the first value, and not performing the first operation if the verify signal takes the second value; and

means for terminating the first operation and the second operation and finishing the verify operation when the verify signal changes from the first value to the second value.

155. (New) The mobile telephone according to claim 154, wherein the first period is 1 μ sec or shorter.

156. (New) The mobile telephone according to claim 154, wherein the memory element stores multi-state data.

157. (New) The mobile telephone according to claim 154, wherein the first operation is performed by one of charge injection and charge discharge using a tunnel current.

158. (New) The mobile telephone according to claim 154, wherein during the second operation, a potential difference exists between a source and a drain of the memory element.

159. (New) The mobile telephone according to claim 154, wherein the first operation is performed by charge injection using a hot electron.

160. (New) The mobile telephone according to claim 154, wherein the memory element is an n-channel type memory element.

161. (New) The mobile telephone according to claim 154, wherein the memory element is a p-channel type memory element.

162. (New) The mobile telephone according to claim 154, wherein the nonvolatile memory is a NOR type nonvolatile memory.

163. (New) The mobile telephone according to claim 154, wherein the nonvolatile memory is a NAND type nonvolatile memory.

164. (New) A mobile telephone comprising:

a body;

a display portion attached to the body;

an operation switch attached to the body; and

a nonvolatile memory embedded in the mobile telephone,

wherein the nonvolatile memory comprises:

means for simultaneously performing a first operation for decreasing the threshold voltage of the memory element and a second operation for judging a relation between the threshold voltage of the memory element and the set voltage;

means for generating a verify signal that takes a first value during a first period;

means for, during a second period, generating a verify signal that takes the first value if the threshold voltage of the memory element is larger than the set voltage, and takes a second value if the threshold voltage of the memory element is smaller than the set voltage;

means for performing the first operation if the verify signal takes the first value, and not performing the first operation if the verify signal takes the second value; and

means for terminating the first operation and the second operation and finishing the verify operation when the verify signal changes from the first value to the second value.

165. (New) The mobile telephone according to claim 164, wherein the first period is 1 μ sec or shorter.

166. (New) The mobile telephone according to claim 164, wherein the memory element stores multi-state data.

167. (New) The mobile telephone according to claim 164, wherein the first operation is performed by one of charge injection and charge discharge using a tunnel current.

168. (New) The mobile telephone according to claim 164, wherein during the second operation, a potential difference exists between a source and a drain of the memory element.

169. (New) The mobile telephone according to claim 164, wherein the first operation is performed by charge injection using a hot electron.

170. (New) The mobile telephone according to claim 164, wherein the memory element is an n-channel type memory element.

171. (New) The mobile telephone according to claim 164, wherein the memory element is a p-channel type memory element.

172. (New) The mobile telephone according to claim 164, wherein the nonvolatile memory is a NOR type nonvolatile memory.

173. (New) The mobile telephone according to claim 164, wherein the nonvolatile memory is a NAND type nonvolatile memory.

Favorable consideration is earnestly solicited.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Mark J. Murphy', with a long, sweeping horizontal line extending to the right.

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